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(54) **SENSE AMPLIFIER AND RELATED METHOD**

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CPC **G11C 7/06** (2013.01); **G11C 7/065**

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(58) **Field of Classification Search**

None
See application file for complete search history.

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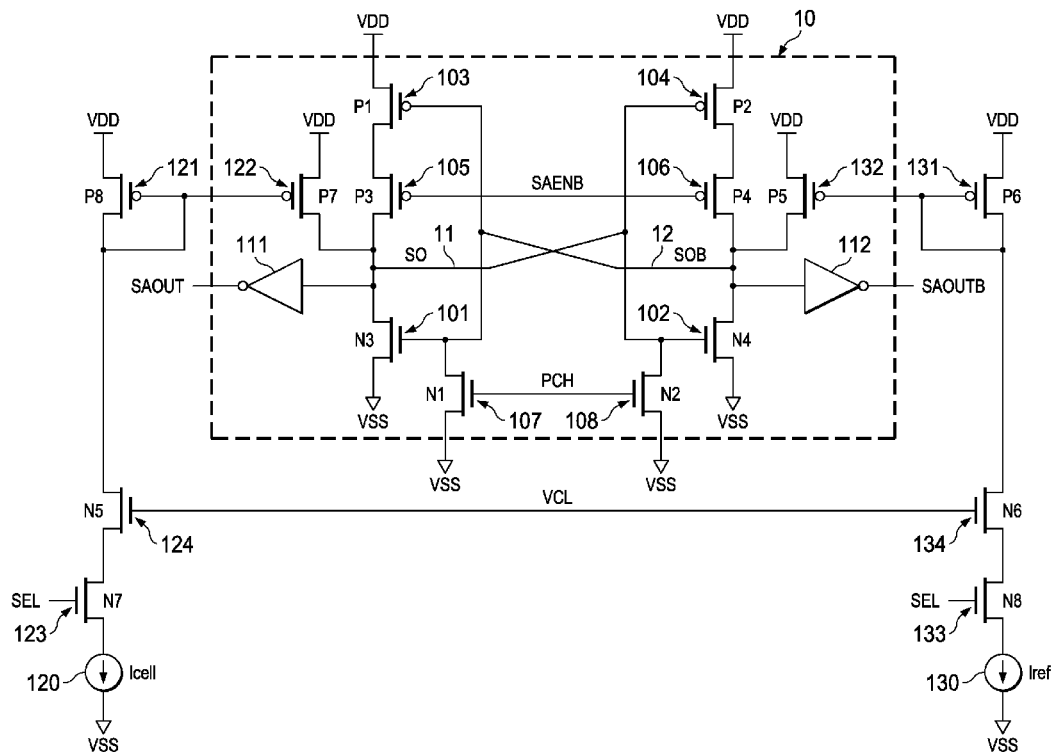
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(57) **ABSTRACT**

A device includes first and second current mirrors electrically connected to reference and cell current sources of a memory array. A first inverter is electrically connected to the first current mirror, and a second inverter is electrically connected to the second current mirror. The first and second inverters are cross-coupled.

20 Claims, 4 Drawing Sheets



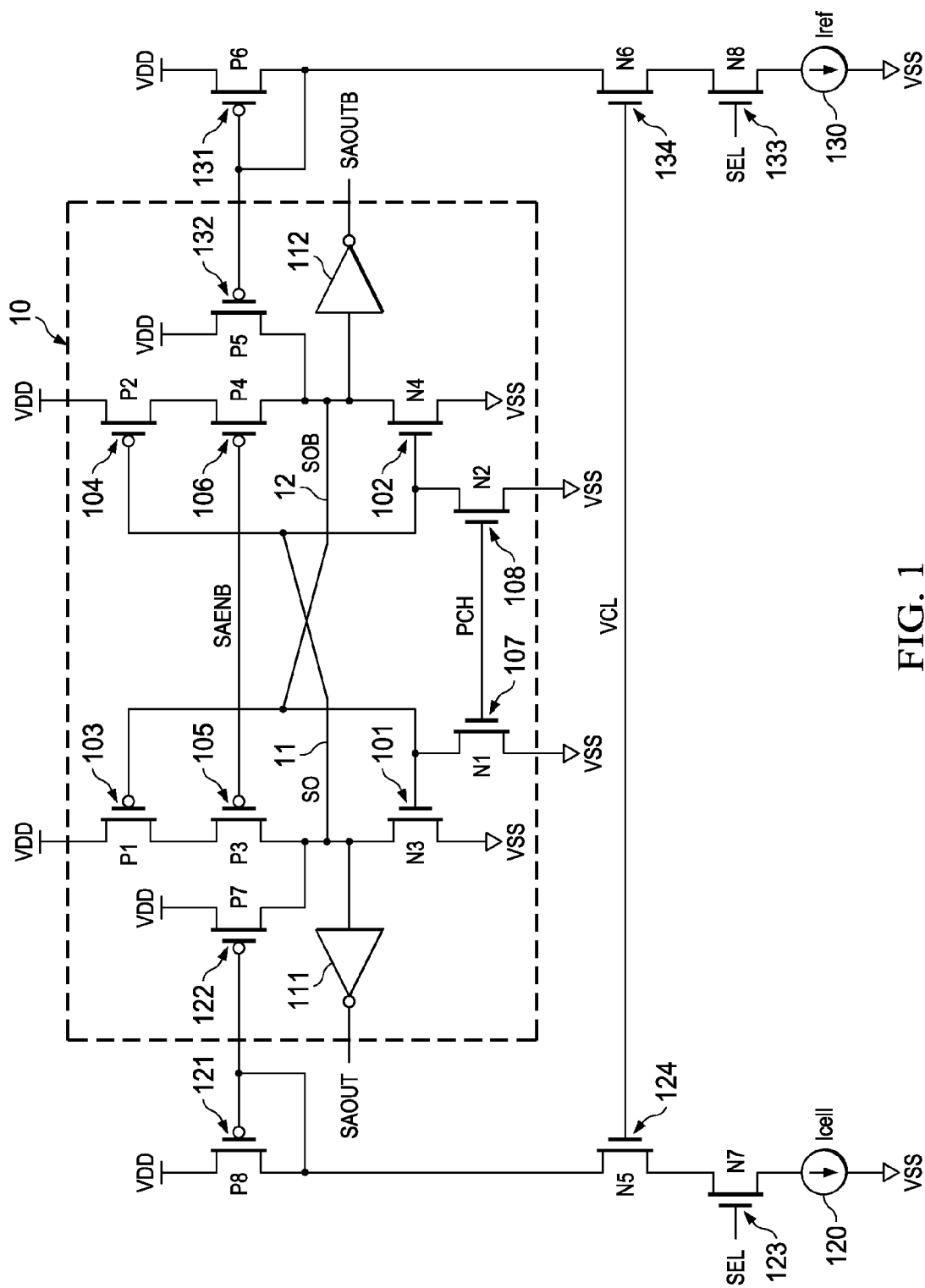


FIG. 1

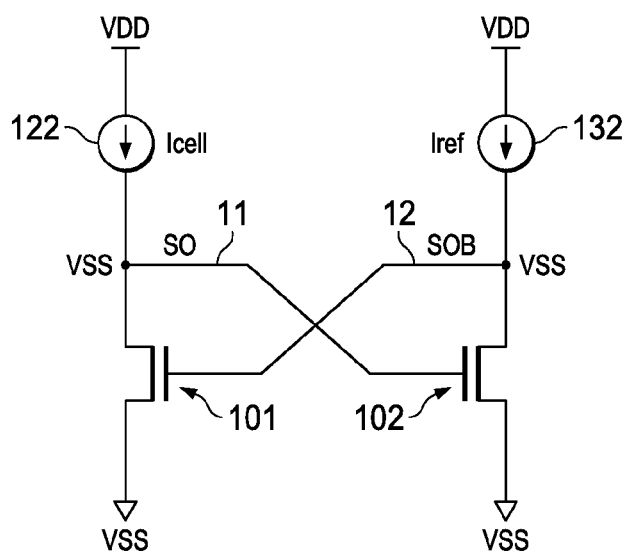


FIG. 2

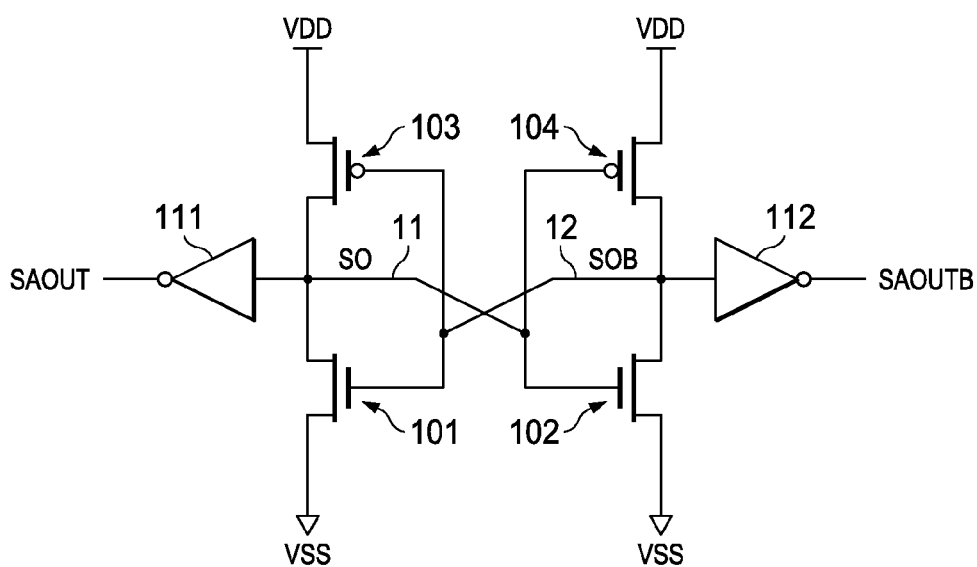


FIG. 3

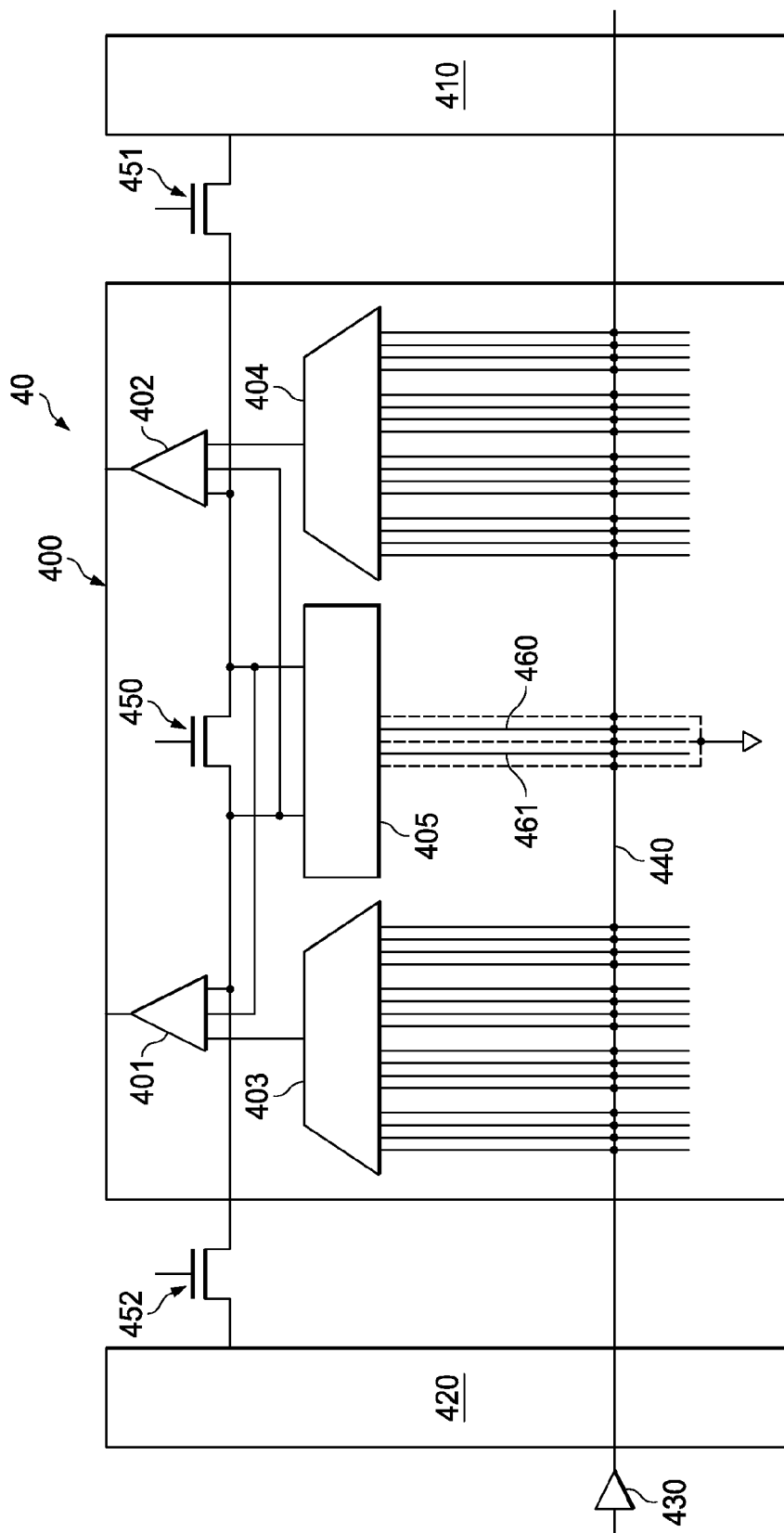


FIG. 4

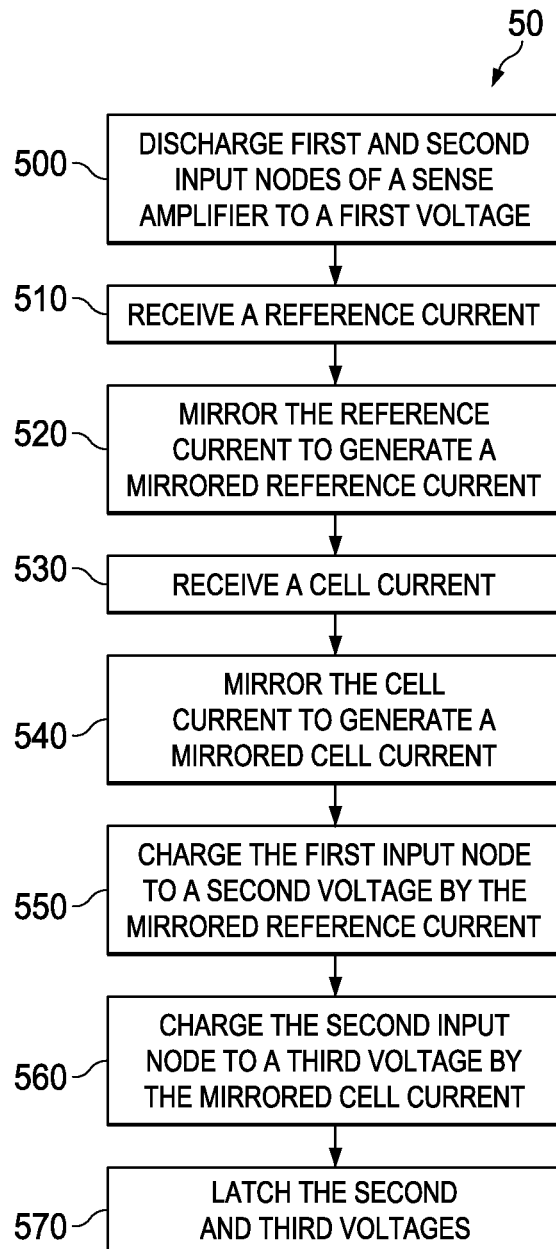


FIG. 5

SENSE AMPLIFIER AND RELATED METHOD

BACKGROUND

The semiconductor industry has experienced rapid growth due to improvements in the integration density of a variety of electronic components (e.g., transistors, diodes, resistors, capacitors, etc.). For the most part, this improvement in integration density has come from shrinking the semiconductor process node (e.g., shrinking the process node towards the sub-20 nm node).

Shrinking the semiconductor process node entails reductions in operating voltage and current consumption of electronic circuits developed in the semiconductor process node. For example, operating voltages have dropped from 5V to 3.3V, 2.5V, 1.8V, and even 0.9V. A wave of mobile device popularity has increased pressure in the industry to develop low power circuits that only drain minimal operating current from batteries that power the mobile devices. Lower operating current extends battery life of battery-operated mobile devices, such as smartphones, tablet computers, ultrabooks, and the like.

BRIEF DESCRIPTION OF THE DRAWINGS

For a more complete understanding of the present embodiments, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

FIG. 1 is a diagram showing a differential current sense amplifier circuit in accordance with various embodiments of the present disclosure;

FIG. 2 is a diagram showing operation of the sense amplifier in a charging phase in accordance with various embodiments of the present disclosure;

FIG. 3 is a diagram showing operation of the sense amplifier in a latching phase in accordance with various embodiments of the present disclosure;

FIG. 4 is a diagram showing a readout circuit in accordance with various embodiments of the present disclosure; and

FIG. 5 is a flowchart of a method in accordance with various embodiments of the present disclosure.

DETAILED DESCRIPTION OF ILLUSTRATIVE EMBODIMENTS

The making and using of the present embodiments are discussed in detail below. It should be appreciated, however, that the present disclosure provides many applicable inventive concepts that can be embodied in a wide variety of specific contexts. The specific embodiments discussed are merely illustrative of specific ways to make and use the disclosed subject matter, and do not limit the scope of the different embodiments.

Embodiments will be described with respect to a specific context, namely sense amplifier circuits and related methods. Other embodiments may also be applied, however, to other types of sensing or amplifying circuits.

Throughout the various figures and discussion, like reference numbers refer to like objects or components. Also, although singular components may be depicted throughout some of the figures, this is for simplicity of illustration and ease of discussion. A person having ordinary skill in the art

will readily appreciate that such discussion and depiction can be and usually is applicable for many components within a structure.

In the following disclosure, a novel sense amplifier circuit and method are introduced. The sense amplifier circuit uses current mirror to prevent read disturb in a memory cell array connected to the sense amplifier.

FIG. 1 is a diagram showing a differential current sense amplifier circuit **10** (or “sense amplifier **10**”) in accordance with various embodiments of the present disclosure. In some embodiments, the sense amplifier **10** reads data stored on at least one memory cell. In some embodiments, the at least one memory cell is a resistive random access memory (RRAM) cell, a magnetoresistive random access memory (MRAM) cell, a flash random access memory (RAM) cell, or the like. During a read operation, a memory cell can be considered a current source **120** (or “cell current source **120**”) that generates a cell current I_{cell} that has amplitude corresponding to a programmed state of the memory cell. For example, if the data stored on the memory cell is binary “1,” the cell current I_{cell} may be a relatively high current. If the data stored on the memory cell is binary “0,” the cell current I_{cell} may be a relatively low current. To read the data on the memory cell, the cell current I_{cell} may be compared with a reference current I_{ref} generated by a reference current source **130**. The sense amplifier **10** compares the cell current I_{cell} with the reference current I_{ref} , and outputs a differential signal SAOUT/SAOUTB that indicates whether the data on the memory cell is binary “1” or “0.” In some embodiments, the reference current source **130** is another memory cell of a memory array including the memory cell that acts as the cell current source **120**. In some embodiments, the memory cell that acts as the reference current source **130** is not used in the memory array to store data (e.g., a dummy memory cell).

In some embodiments, the cell current I_{cell} and the reference current I_{ref} are mirrored to the sense amplifier **10**. Transistors **121-124** form a cell-side mirror circuit for mirroring the cell current I_{cell} to the sense amplifier **10**. Transistors **131-134** form a reference-side mirror circuit for mirroring the reference current I_{ref} to the sense amplifier **10**. Mirroring the cell and reference currents I_{cell} , I_{ref} to the sense amplifier **10** provides isolation that is beneficial to preventing read disturb, and also allows the reference current source **130** to be shared by at least two sense amplifiers of the memory array including the memory cell.

The transistor **121** has a source electrode that is electrically connected to a first voltage supply node. In some embodiments, the first voltage supply node supplies a first voltage VDD (e.g., 5 Volts, 3.3 Volts, 2.5 Volts, 1.8 Volts, 0.9 Volts, or the like). A drain electrode of the transistor **121** is electrically connected to a gate electrode of the transistor **121**.

The transistor **122** has a source electrode that is electrically connected to the first voltage supply node. A gate electrode of the transistor **122** is electrically connected to the gate electrode of the transistor **121**. A drain electrode of the transistor **122** is electrically connected to a node **11** of the sense amplifier **10**. In some embodiments, the transistors **121**, **122** are P-type metal-oxide-semiconductor (PMOS) transistors.

The transistor **131** has a source electrode that is electrically connected to a first voltage supply node. In some embodiments, the first voltage supply node supplies a first voltage VDD (e.g., 5 Volts, 3.3 Volts, 2.5 Volts, 1.8 Volts, 0.9

Volts, or the like). A drain electrode of the transistor **131** is electrically connected to a gate electrode of the transistor **131**.

The transistor **132** has a source electrode that is electrically connected to the first voltage supply node. A gate electrode of the transistor **132** is electrically connected to the gate electrode of the transistor **131**. A drain electrode of the transistor **132** is electrically connected to a node **12** of the sense amplifier **10**. In some embodiments, the transistors **131**, **132** are PMOS transistors.

The transistors **123**, **133** are select transistors. A gate electrode of the transistor **123** is configured to receive a select signal SEL from a controller (e.g., an address decoder, or the like). A source electrode of the transistor **123** is electrically connected to the cell current source **120** (e.g., the memory cell). A drain electrode of the transistor **123** is electrically connected to a source electrode of the transistor **124**.

A gate electrode of the transistor **133** is configured to receive the select signal SEL. A source electrode of the transistor **133** is electrically connected to the reference current source **130**. A drain electrode of the transistor **133** is electrically connected to a source electrode of the transistor **134**.

The transistors **124**, **134** are clamp transistors that prevent high voltages from damaging the cell current source **120** and the reference current source **130**. A gate electrode of the transistor **124** is electrically connected to a gate electrode of the transistor **134**. A drain electrode of the transistor **124** is electrically connected to the drain electrode of the transistor **121**. The source electrode of the transistor **124** is electrically connected to the drain electrode of the transistor **123**.

The gate electrode of the transistor **134** is electrically connected to the gate electrode of the transistor **124**. The gate electrodes of the transistors **124**, **134** are configured to receive a clamp voltage VCL from a controller. A drain electrode of the transistor **134** is electrically connected to the drain electrode of the transistor **131**. The source electrode of the transistor **134** is electrically connected to the drain electrode of the transistor **133**. In some embodiments, the transistors **123**, **124**, **133**, **134** are N-type metal-oxide-semiconductor (NMOS) transistors.

When the transistors **123**, **124**, **133**, **134** are turned on, the cell current I_{cell} is mirrored to the transistor **122**, and the reference current I_{ref} is mirrored to the transistor **132**.

In the sense amplifier **10**, the transistors **101**, **103**, **105** form a first inverter, and the transistors **102**, **104**, **106** form a second inverter. The first inverter is configured to be enabled or disabled by the transistor **105**. The second inverter is configured to be enabled or disabled by the transistor **106**. In some embodiments, the transistors **101**, **102** are NMOS transistors, and the transistors **103-106** are PMOS transistors.

A gate electrode of the transistor **101** is electrically connected to the node **12**. The node **12** corresponds to at least one of the drain electrode of the transistor **132**, a drain electrode of the transistor **102** or a drain electrode of the transistor **106**. A drain electrode of the transistor **101** is electrically connected to the node **11**. The node **11** corresponds to at least one of the drain electrode of the transistor **122**, a gate electrode of the transistor **102** or a drain electrode of the transistor **105**. A source electrode of the transistor **101** is electrically connected to the second voltage supply node.

A gate electrode of the transistor **103** is electrically connected to the gate electrode of the transistor **101**. A source electrode of the transistor **103** is electrically connected to the first voltage supply node. A drain electrode of

the transistor **103** is electrically connected to a source electrode of the transistor **105**.

A gate electrode of the transistor **102** is electrically connected to the node **11**. A drain electrode of the transistor **102** is electrically connected to a node **12**. A source electrode of the transistor **102** is electrically connected to the second voltage supply node.

A gate electrode of the transistor **104** is electrically connected to the gate electrode of the transistor **102**. A source electrode of the transistor **104** is electrically connected to the first voltage supply node. A drain electrode of the transistor **104** is electrically connected to a source electrode of the transistor **106**.

The transistors **105**, **106** act as enable circuits of the first inverter and the second inverter, and are configured to receive a sense amplifier enable bar signal SAENB from a controller. In some embodiments, the transistors **105**, **106** are PMOS transistors. A gate electrode of the transistor **105** is electrically connected to a gate electrode of the transistor **106**. A source electrode of the transistor **105** is electrically connected to the drain electrode of the transistor **103**. A source electrode of the transistor **106** is electrically connected to the drain electrode of the transistor **104**. A drain electrode of the transistor **105** is electrically connected to the drain electrode of the transistor **101**. A drain electrode of the transistor **106** is electrically connected to the drain electrode of the transistor **102**.

In some embodiments, the sense amplifier **10** includes transistors **107**, **108**. The transistors **107**, **108** are pre-charge transistors. In some embodiments, the transistors **107**, **108** are NMOS transistors. A gate electrode of the transistor **107** is electrically connected to a gate electrode of the transistor **108**. A pre-charge signal PCH is applied to the gate electrodes of the transistors **107**, **108** by a controller. Source electrodes of the transistors **107**, **108** are electrically connected to the second voltage supply node. A drain electrode of the transistor **107** is electrically connected to the gate electrode of the transistor **101** (the node **12**). A drain electrode of the transistor **108** is electrically connected to the gate electrode of the transistor **102** (the node **11**).

Comparators **111**, **112** generate the sense amplifier out signal SAOUT and the sense amplifier out bar signal SAOUTB. In some embodiments, the comparators **111**, **112** are inverters. An input terminal of the comparator **111** is electrically connected to the node **11**, and is configured to receive a sense out signal SO. In some embodiments, the sense out signal SO is a voltage. An input terminal of the comparator **112** is electrically connected to the node **12**, and is configured to receive a sense out bar signal SOB. In some embodiments, the sense out bar signal SOB is a voltage.

The sense amplifier **10** performs a read operation through at least three phases: a pre-charging phase, a charging phase, and a latching phase. In the pre-charging phase, the pre-charge signal PCH is asserted (e.g., logic high, a high voltage, VDD) to turn on the transistors **107**, **108**. The transistors **107**, **108** conduct current to pull down voltage at the nodes **11**, **12** to the second voltage VSS (e.g., ground, -VDD, or the like). With voltage at the nodes **11**, **12** low, the transistors **101**, **102** are turned off. The sense amp enable bar signal SAENB is a high voltage (e.g., sufficiently high to turn off the transistors **105**, **106**) during the pre-charging and charging phases.

FIG. 2 is a diagram showing operation of the sense amplifier **10** in the charging phase in accordance with various embodiments of the present disclosure. Depiction of the sense amplifier **10** is simplified in FIG. 2 for clarity of discussion. In the charging phase, the pre-charge signal PCH

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is disasserted, so that the transistors **107**, **108** can be considered substantially open circuits. The sense amplifier enable bar signal SAENB is at a voltage high enough to turn off the transistors **105**, **106**, so that the transistors **105**, **106** can be considered substantially open circuits.

In the charging phase, the nodes **11**, **12** are initially at the second voltage VSS following the pre-charging phase. Depending on relative strength of the cell current I_{cell} versus the reference current I_{ref} , one or the other of the nodes **11**, **12** is charged more rapidly than the other node. For example, if the cell current I_{cell} is much stronger than the reference current I_{ref} , the first current (substantially the cell current I_{cell}) mirrored through the transistor **122** charges the node **11** more quickly than the second current (substantially the reference current I_{ref}) mirrored through the transistor **132** charges the node **12**. In this case, voltage at the node **11** (SO) is pulled up toward the first voltage VDD much more quickly than voltage at the node **12** (SOB). As a result, the transistor **102** turns on before the transistor **101** turns on (if at all). The transistor **102** pulls down the voltage at the node **12** (SOB) toward the second voltage VSS. The node **11** reaches a steady-state voltage of about the first voltage VDD (e.g., binary “1”), and the node **12** reaches a steady-state voltage of about the second voltage VSS (e.g., binary “0”).

If the cell current I_{cell} is weaker than the reference current I_{ref} , the first current (substantially the cell current I_{cell}) mirrored through the transistor **122** charges the node **11** less quickly than the second current (substantially the reference current I_{ref}) mirrored through the transistor **132** charges the node **12**. In this case, voltage at the node **11** (SO) is pulled up toward the first voltage VDD slower than voltage at the node **12** (SOB). As a result, the transistor **101** turns on before the transistor **102** turns on (if at all). The transistor **101** pulls down the voltage at the node **11** (SO) toward the second voltage VSS. The node **12** reaches a steady-state voltage of about the first voltage VDD (e.g., binary “1”), and the node **11** reaches a steady-state voltage of about the second voltage VSS (e.g., binary “0”).

FIG. 3 is a diagram showing operation of the sense amplifier **10** in the latching phase in accordance with various embodiments of the present disclosure. In the latching phase, the sense amplifier enable bar signal SAENB is at a voltage low enough to turn on the transistors **105**, **106**. Biased by the low voltage, the transistors **105**, **106** are on, and are thus represented as short circuits in the circuit diagram of FIG. 3 for ease of illustration. With the transistors **105**, **106** turned on by the sense amplifier enable bar signal SAENB, the transistors **103**, **104** and the transistors **101**, **102** form two cross-coupled inverters. The transistor **101** and the transistor **103** form a first inverter, and the transistors **102**, **104** form a second inverter. Output of the first inverter is at the node **11** (SO). A first-side amplifier **111** has an input terminal electrically connected to the output of the first inverter. In some embodiments, the first-side amplifier **111** is an inverter having circuit structure similar to the first inverter. In some embodiments, the first-side amplifier **111** acts as a buffer. Input of the first inverter is electrically connected to the node **12**.

Output of the second inverter is at the node **12** (SO). A second-side amplifier **112** has an input terminal electrically connected to the output of the second inverter. In some embodiments, the second-side amplifier **112** is an inverter having circuit structure similar to the second inverter. In some embodiments, the second-side amplifier **112** acts as a buffer. Input of the second inverter is electrically connected to the node **11**.

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Prior to the latching phase, when the cell current I_{cell} is larger than the reference current I_{ref} , the node **11** is charged to about the first voltage VDD, and the node **12** is charged to about the second voltage VSS. Under these conditions, the relatively high voltage (e.g., about VDD) at the node **11** turns on the transistor **102**, and turns off the transistor **104**, so that the voltage at the node **12** (SOB) is held at a relatively low voltage (e.g., about VSS). The relatively low voltage at the node **12** turns on the transistor **103**, and turns off the transistor **101**, so that the voltage at the node **11** (SOB) is held at the relatively high voltage (e.g., about VDD). The relatively high voltage at the node **11** is inverted by the first-side amplifier **111** to output the sense amplifier output signal SAOUT as about the second voltage VSS for the cell current I_{cell} that is larger than the reference current I_{ref} . The relatively low voltage at the node **12** is inverted by the second-side amplifier **112** to output the sense amplifier output bar signal SAOUTB as about the first voltage VDD.

Prior to the latching phase, when the cell current I_{cell} is smaller than the reference current I_{ref} , the node **12** is charged to about the first voltage VDD, and the node **11** is charged to about the second voltage VSS. Under these conditions, the relatively high voltage (e.g., about VDD) at the node **12** turns on the transistor **101**, and turns off the transistor **103**, so that the voltage at the node **11** (SO) is held at a relatively low voltage (e.g., about VSS). The relatively low voltage at the node **11** turns on the transistor **104**, and turns off the transistor **102**, so that the voltage at the node **12** (SO) is held at the relatively high voltage (e.g., about VDD). The relatively high voltage at the node **12** is inverted by the second-side amplifier **112** to output the sense amplifier output bar signal SAOUTB as about the second voltage VSS for the cell current I_{cell} that is smaller than the reference current I_{ref} . The relatively low voltage at the node **11** is inverted by the first-side amplifier **111** to output the sense amplifier output signal SAOUT as about the first voltage VDD.

FIG. 4 is a diagram showing a readout circuit **40** in accordance with various embodiments of the present disclosure. In some embodiments, a sense amplifier **401** is configured to read one of at least two memory cells. For example, in the configuration shown in FIG. 4, the sense amplifier **401** corresponds to 16 column lines, each column line corresponding to a single memory cell (e.g., an RRAM cell). In some embodiments, a sense amplifier **402** is configured to read a further group of memory cells (e.g., 16 memory cells). A multiplexer **403** selects one of the memory cells to be read by the sense amplifier **401** at a time. Input terminals of the multiplexer **403** electrically connect to output terminals of the memory cells. An output terminal of the multiplexer **403** is electrically connected to a first input of the sense amplifier **401**. In some embodiments, the sense amplifier **401** is substantially the same as the sense amplifier **10**.

A multiplexer **404** selects one of the memory cells to be read by the sense amplifier **402** at a time. Input terminals of the multiplexer **404** electrically connect to output terminals of the memory cells. An output terminal of the multiplexer **404** is electrically connected to a first input of the sense amplifier **402**. In some embodiments, the sense amplifier **402** is substantially the same as the sense amplifier **10**.

The sense amplifiers **401**, **402** of a sense amplifier block **400** share a reference current source **405**. The reference current source **405** includes a first reference current on a first line **460**, and a second reference current on a second line **461**. In some embodiments, dummy lines (shown in phantom) electrically connected to ground surround the first and

second lines 460, 461. In some embodiments, the first reference current is generated by a memory cell storing binary "1," and the second reference current is generated by a memory cell storing binary "0." For example, the first reference current is a very low current I_L , and the second reference current is a relatively high current I_H . The reference current source 405 merges the first and second reference currents to generate a reference current having amplitude substantially equal to $I_H + I_L$. The reference current is supplied to two sense amplifiers (the sense amplifiers 401, 402), so that each sense amplifier 401, 402 receives about half of the reference current ($(I_H + I_L)/2$). The half of the reference current may approximate an average (or "mid-point") of the current generated by a bit cell storing binary "1" and the current generated by a bit cell storing binary "0."

In some embodiments, a second sense amplifier block 410 is substantially the same as the sense amplifier block 400. The second sense amplifier block 410 is adjacent the sense amplifier block 400, and also has a reference current source. In some embodiments, a third sense amplifier block 420 is substantially the same as the sense amplifier block 400. The third sense amplifier block 420 is adjacent the sense amplifier block 400, and also has a reference current source. In some embodiments, the sense amplifier blocks 400, 410, 420 all correspond to a single word line 440 driven by a word line driver 430.

Transistors 450, 451, 452 are configured to selectively merge (turned on) or isolate (turned off) the reference current sources of the sense amplifier blocks 400, 410, 420. For example, when the transistors 450, 451, 452 are turned on, the reference currents generated by the reference current sources are merged. For a configuration including 32 sense amplifiers, total reference current approaching $16(I_H + I_L)$ is shared by the 32 sense amplifiers, so that each sense amplifier receives a midpoint reference current of about $(I_H + I_L)/2$.

One advantage of using the circuit architecture of the sense amplifier 10 in the readout circuit 40 is that the reference-side mirror circuit (including the transistors 131, 132) isolates the sense amplifier 10 and selected bit cell from the reference current source (e.g. the reference current source 405). This isolation mostly eliminates disturbance from operation of the sense amplifier 10.

FIG. 5 is a flowchart of a method 50 in accordance with various embodiments of the present disclosure. In some embodiments, the method 50 is performed by the sense amplifier 10 of FIG. 1. Description of the method 50 with reference to the sense amplifier 10 does not exclude the method 50 from being performed using other sense amplifier architectures.

First and second input nodes (e.g., the nodes 11 and 12) of a sense amplifier are discharged 500 to a first voltage (e.g., the second voltage VSS, ground, or the like). In some embodiments, the discharging 500 is performed by turning on a pair of transistors (e.g., the transistors 107, 108) electrically connected to the first and second input nodes in a pre-charging phase.

A reference current (e.g., the reference current I_{ref}) is received 510 by a first transistor of a reference-side current mirror (e.g., the transistor 131). In some embodiments, the reference current is received 510 when a select transistor (e.g., the transistor 133) is turned on. In some embodiments, the receiving 510 includes conducting the reference current by the first transistor. In some embodiments, the reference current is generated by a single bit cell or by multiple bit cells (such as in FIG. 4). The reference current is mirrored 520 to generate a mirrored reference current. In some

embodiments, the reference current is mirrored by a second transistor (e.g., the transistor 132).

A cell current (e.g., the cell current I_{cell}) is received 530 by a third transistor of a cell-side current mirror (e.g., the transistor 121). In some embodiments, the cell current is received 530 when a select transistor (e.g., the transistor 123) is turned on. In some embodiments, the receiving 530 includes conducting the cell current by the third transistor. The cell current is mirrored 540 to generate a mirrored reference current. In some embodiments, the cell current is mirrored by a fourth transistor (e.g., the transistor 122).

The first input node is charged 550 to a second voltage by the mirrored reference current, and the second input node is charged 560 to a third voltage by the mirrored cell current. In some embodiments, the pair of transistors electrically connected to the first and second input nodes are turned off during the operations 520-560. The second and third voltages are then latched 570. In some embodiments, the latching 570 is performed by turning on a second pair of transistors (e.g., the transistors 105, 106) to turn on two cross-coupled inverter circuits having input and output nodes corresponding to the first and second input nodes.

Embodiments may achieve advantages. By mirroring the cell and reference currents to the sense amplifier 10, disturbance from operation of the sense amplifier 10 can be effectively reduced. Further, mirroring the reference current allows all reference currents on a same word line to be merged, which improves reference current distribution, and improves yield.

In accordance with various embodiments of the present disclosure, a device includes a first current mirror, a second current mirror, a first inverter, and a second inverter. The first current mirror is electrically connected to a reference current source of a memory array. The second current mirror is electrically connected to a cell current source of the memory array. The first inverter has a first input terminal electrically connected to the first current mirror, and a first output terminal. The second inverter has a second input terminal electrically connected to the second current mirror and the first output terminal, and a second output terminal electrically connected to the first current mirror and the first input terminal.

In accordance with various embodiments of the present disclosure, a device includes at least two sense amplifier blocks. Each sense amplifier block includes a first multiplexer, a second multiplexer, a reference current source, a first sense amplifier, and a second sense amplifier. The first multiplexer has at least two inputs electrically connected to first bit cells of a memory array. The second multiplexer has at least two inputs electrically connected to second bit cells of the memory array. The reference current source has a first reference line electrically connected to a first reference bit cell, and a second reference line electrically connected to a second reference bit cell. The first sense amplifier has a first input electrically connected to an output of the first multiplexer, and a second input electrically connected to a first output terminal of the reference current source. The second sense amplifier has a first input electrically connected to an output of the second multiplexer, and a second input electrically connected to a second output terminal of the reference current source. The device further includes at least two switches configured to merge reference currents supplied through the first and second reference lines of the at least two sense amplifier blocks.

In accordance with various embodiments of the present disclosure, a method includes (a) receiving a reference current; (b) mirroring the reference current to generate a

mirrored reference current; (c) receiving a cell current; (d) mirroring the cell current to generate a mirrored cell current; (e) charging a first input node of a sense amplifier to a first voltage by the mirrored reference current; (f) charging a second input node of the sense amplifier to a second voltage by the mirrored cell current; and (g) latching the first and second voltages.

As used in this application, “or” is intended to mean an inclusive “or” rather than an exclusive “or”. In addition, “a” and “an” as used in this application are generally to be construed to mean “one or more” unless specified otherwise or clear from context to be directed to a singular form. Also, at least one of A and B and/or the like generally means A or B or both A and B. Furthermore, to the extent that “includes”, “having”, “has”, “with”, or variants thereof are used in either the detailed description or the claims, such terms are intended to be inclusive in a manner similar to the term “comprising”. Moreover, the term “between” as used in this application is generally inclusive (e.g., “between A and B” includes inner edges of A and B).

Although the present embodiments and their advantages have been described in detail, it should be understood that various changes, substitutions, and alterations can be made herein without departing from the spirit and scope of the disclosure as defined by the appended claims. Moreover, the scope of the present application is not intended to be limited to the particular embodiments of the process, machine, manufacture, composition of matter, means, methods, and steps described in the specification. As one of ordinary skill in the art will readily appreciate from the disclosure, processes, machines, manufacture, compositions of matter, means, methods, or steps, presently existing or later to be developed, that perform substantially the same function or achieve substantially the same result as the corresponding embodiments described herein may be utilized according to the present disclosure. Accordingly, the appended claims are intended to include within their scope such processes, machines, manufacture, compositions of matter, means, methods, or steps.

What is claimed is:

1. A device comprising:

- a first current mirror electrically connected to a reference current source of a memory array;
- a second current mirror electrically connected to a cell current source of the memory array, wherein the first current mirror and the second current mirror have an equivalent structure;
- a first inverter having:
 - a first input terminal electrically connected to the first current mirror; and
 - a first output terminal; and
- a second inverter having:
 - a second input terminal electrically connected to the second current mirror and the first output terminal; and
 - a second output terminal electrically connected to the first current mirror and the first input terminal;
- a first clamp transistor directly connected to the first current mirror and a first select transistor;
- a second clamp transistor electrically connected to the second current mirror and a second select transistor;
- the first select transistor directly connected to the first clamp transistor and the reference current source; and
- a second select transistor electrically connected to the second clamp transistor and the cell current source.

2. The device of claim 1, wherein:

the first inverter has:

- a first transistor;
 - a second transistor having a gate electrode electrically connected to a gate electrode of the first transistor; and
 - a first enable transistor having a source electrode electrically connected to a drain electrode of the first transistor, and a drain electrode electrically connected to a drain electrode of the second transistor; and
- the second inverter has:
- a third transistor;
 - a fourth transistor having a gate electrode electrically connected to a gate electrode of the third transistor; and
 - a second enable transistor having a source electrode electrically connected to a drain electrode of the third transistor, and a drain electrode electrically connected to a drain electrode of the fourth transistor.
- 3.** The device of claim 1, further comprising:
- a first pre-charge transistor electrically connected to the first input terminal; and
 - a second pre-charge transistor electrically connected to the second input terminal.
- 4.** The device of claim 1, wherein the first current mirror comprises:
- a first current mirror transistor, a source terminal of the first current mirror transistor being directly connected to a voltage supply, a drain terminal of the first current mirror transistor being connected to a clamp transistor; and
 - a second current mirror transistor, a gate terminal of the second current mirror transistor being connected to a gate of the first current mirror transistor, and a source terminal of the second current mirror transistor being directly connected to the voltage supply.
- 5.** The device of claim 1, wherein a gate terminal of the first clamp transistor is electrically connected to a gate terminal of the second clamp transistor.
- 6.** The device of claim 2, further comprising:
- a third inverter having an input terminal electrically connected to the first output terminal; and
 - a fourth inverter having an input terminal electrically connected to the drain electrode of the fourth transistor.
- 7.** A device comprising:
- at least two sense amplifier blocks, each sense amplifier block including:
 - a first multiplexer having at least two inputs electrically connected to first bit cells of a memory array;
 - a second multiplexer having at least two inputs electrically connected to second bit cells of the memory array, the second multiplexer being physically disconnected from the first multiplexer;
 - a reference current source having:
 - a first reference line electrically connected to a first reference bit cell; and
 - a second reference line electrically connected to a second reference bit cell;
 - a first sense amplifier having a first input electrically connected to an output of the first multiplexer, and a second input electrically connected to a first output terminal of the reference current source; and
 - a second sense amplifier having a first input electrically connected to an output of the second multiplexer, and a second input electrically connected to a second output terminal of the reference current source; and
 - at least one switch configured to merge reference currents supplied through the first and second reference lines of

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the at least two sense amplifier blocks, wherein the merged reference currents continuously pass along a same conductive path, the conductive path extending to each of the at least two sense amplifier blocks.

8. The device of claim 7, wherein each of the first and second sense amplifiers comprises:

- a first current mirror electrically connected to the reference current source;
- a second current mirror electrically connected to the first or second multiplexer;
- a first inverter having:
 - a first input terminal electrically connected to the first current mirror;
 - a first output terminal; and
- a second inverter having:
 - a second input terminal electrically connected to the second current mirror and the first output terminal; and
- a second output terminal electrically connected to the first current mirror and the first input terminal.

9. The device of claim 8, wherein:

- the first inverter has:
- a first transistor;
 - a second transistor having a gate electrode electrically connected to a gate electrode of the first transistor; and
 - a first enable transistor having a source electrode electrically connected to a drain electrode of the first transistor, and a drain electrode electrically connected to a drain electrode of the second transistor; and

the second inverter has:

- a third transistor;
- a fourth transistor having a gate electrode electrically connected to a gate electrode of the third transistor; and
- a second enable transistor having a source electrode electrically connected to a drain electrode of the third transistor, and a drain electrode electrically connected to a drain electrode of the fourth transistor.

10. The device of claim 8, wherein each of the first and second sense amplifiers further comprises:

- a first pre-charge transistor electrically connected to the first input terminal; and
- a second pre-charge transistor electrically connected to the second input terminal.

11. The device of claim 8, wherein each of the first and second sense amplifiers further comprises:

- first clamp transistor electrically connected to the first current mirror and the reference current source; and
- a second clamp transistor electrically connected to the second current mirror and a memory cell.

12. The device of claim 11, wherein each of the first and second sense amplifiers further comprises:

- a first select transistor electrically connected to the first clamp transistor and the reference current source; and
- a second select transistor electrically connected to the second clamp transistor and the memory cell.

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13. The device of claim 8, wherein each of the first and second sense amplifiers further comprises:

- a third inverter having an input terminal electrically connected to the first output terminal; and
- a fourth inverter having an input terminal electrically connected to the second output terminal.

14. A method comprising:

- (a) receiving a reference current;
- (b) mirroring the reference current to generate a mirrored reference current;
- (c) receiving a cell current;
- (d) mirroring the cell current to generate a mirrored cell current;
- (e) receiving a first sense amplifier enable signal from a controller by a first transistor and a second transistor of a sense amplifier, a drain electrode of the first transistor being directly connected to a current mirror that mirrors the cell current and a drain electrode of the second transistor being directly connected to a current mirror that mirrors the reference current, the first sense amplifier enable signal having a voltage that is sufficiently high to turn off the first transistor and the second transistor;
- (f) charging a first input node of the sense amplifier to a first voltage by the mirrored reference current;
- (g) charging a second input node of the sense amplifier to a second voltage by the mirrored cell current;
- (h) receiving a second sense amplifier enable signal by the first transistor and the second transistor of the sense amplifier, the second sense amplifier enable signal having a voltage that is sufficiently low to turn on the first transistor and the second transistor; and
- (i) latching the first and second voltages.

15. The method of claim 14, further comprising:

- (j) discharging the first and second input nodes of the sense amplifier to a third voltage prior to (e) and (f).

16. The method of claim 14, wherein (a) includes receiving the reference current from a reference current source shared between the sense amplifier and another sense amplifier.

17. The method of claim 14, further comprising:

- (k) outputting a differential sense signal by inverting the first voltage by a first inverter and inverting the second voltage by a second inverter.

18. The method of claim 14, wherein (c) includes receiving the cell current generated by a resistive random access memory (RRAM) bit cell.

19. The method of claim 14, wherein (a) includes receiving the reference current from a reference current source shared between the sense amplifier and at least three other sense amplifiers.

20. The method of claim 14, wherein (a) includes receiving a merged current including first current from a first bit cell programmed to binary "1" and second current from a second bit cell programmed to binary "0".

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